

FQP3P20

P-Channel QFET® MOSFET

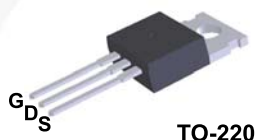
-200 V, -2.8 A, 2.7 Ω

Description

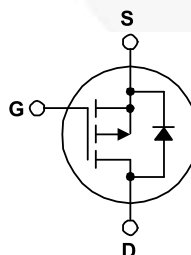
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -2.8 A, -200 V, $R_{DS(on)} = 2.7 \Omega$ (Max.) @ $V_{GS} = -10$ V, $I_D = -1.4$ A
- Low Gate Charge (Typ. 6 nC)
- Low C_{rss} (Typ 7.5 pF)
- 100% Avalanche Tested



TO-220



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQP3P20	Unit
V_{DSS}	Drain-Source Voltage	-200	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	-2.8	A
	- Continuous ($T_C = 100^\circ\text{C}$)	-1.77	A
I_{DM}	Drain Current - Pulsed (Note 1)	-11.2	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	150	mJ
I_{AR}	Avalanche Current (Note 1)	-2.8	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	5.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-5.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	52	W
	- Derate above 25°C	0.42	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQP3P20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3P20	FQP3P20	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C	--	-0.18	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
		$V_{DS} = -160\text{ V}, T_C = 125^\circ\text{C}$	--	--	-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -1.4\text{ A}$	--	2.06	2.7	Ω
g_{FS}	Forward Transconductance	$V_{DS} = -40\text{ V}, I_D = -1.4\text{ A}$	--	1.23	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	190	250	pF
C_{oss}	Output Capacitance		--	45	60	pF
C_{rss}	Reverse Transfer Capacitance		--	7.5	10	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -100\text{ V}, I_D = -2.8\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4)	--	8.5	25	ns
t_r	Turn-On Rise Time		--	35	80	ns
$t_{d(off)}$	Turn-Off Delay Time		--	12	35	ns
t_f	Turn-Off Fall Time		--	25	60	ns
Q_g	Total Gate Charge	$V_{DS} = -160\text{ V}, I_D = -2.8\text{ A},$ $V_{GS} = -10\text{ V}$ (Note 4)	--	6.0	8.0	nC
Q_{gs}	Gate-Source Charge		--	1.7	--	nC
Q_{gd}	Gate-Drain Charge		--	2.9	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-2.8	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-11.2	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -2.8 A	--	--	-5.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -2.8 A,	--	100	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	--	0.34	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = 29\text{ mH}, I_{AS} = 2.8\text{ A}, V_{DD} = -50\text{ V}, R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq -2.8\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

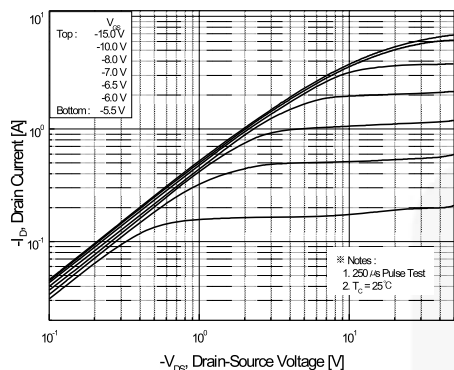


Figure 1. On-Region Characteristics

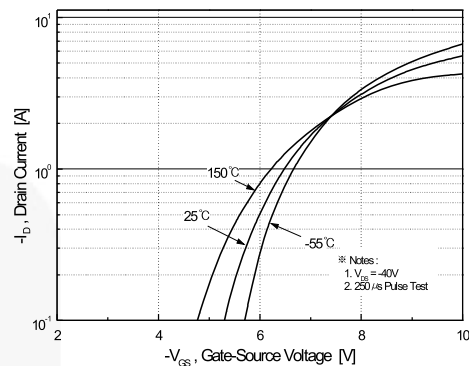


Figure 2. Transfer Characteristics

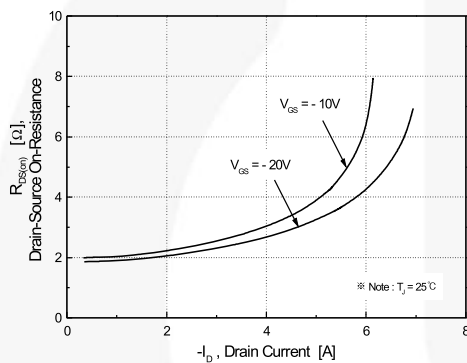


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

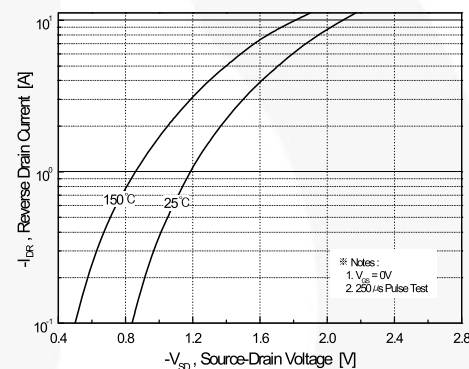


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

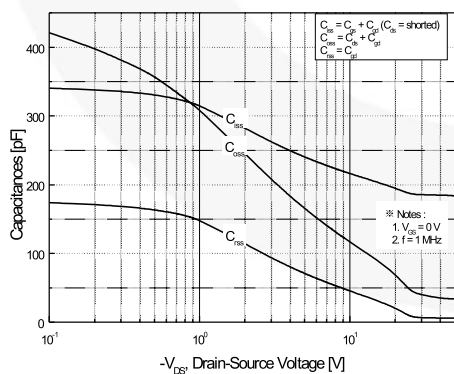


Figure 5. Capacitance Characteristics

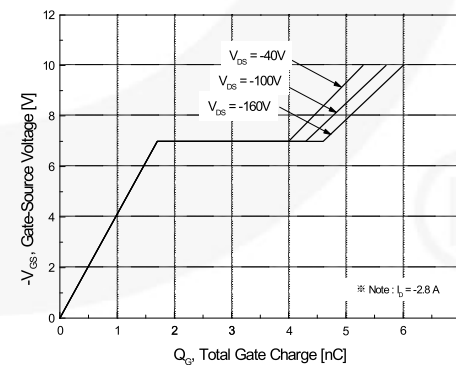


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

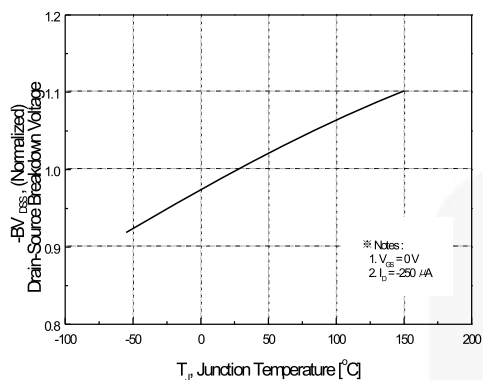


Figure 7. Breakdown Voltage Variation vs. Temperature

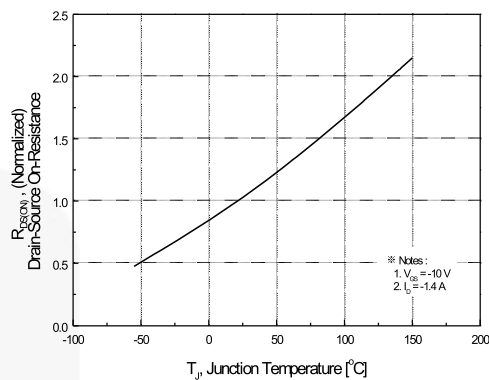


Figure 8. On-Resistance Variation vs. Temperature

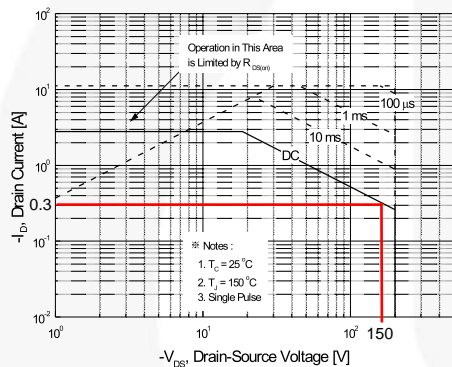


Figure 9. Maximum Safe Operating Area

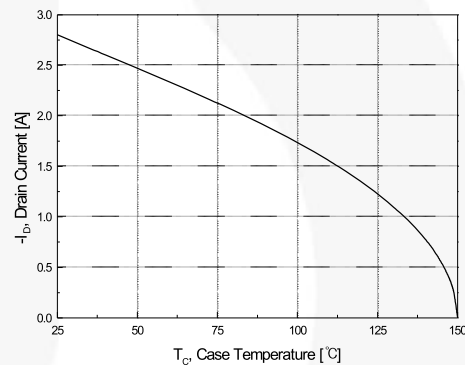


Figure 10. Maximum Drain Current vs. Case Temperature

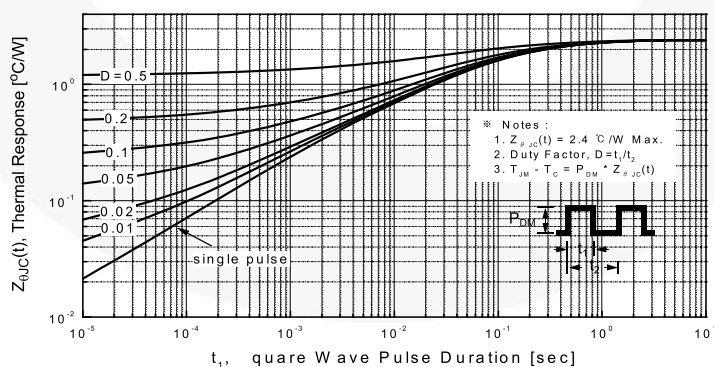


Figure 11. Transient Thermal Response Curve